1. A method comprising:

implanting germanium at a dose greater than about 2E16 atoms/cm2; and

forming a P-type source/drain extension in the region that has been implanted with germanium.

2. The method of claim 1 including implanting germanium using an energy of at least 10 keV.

3. The method of claim 1 including implanting the germanium to a depth greater than about 200 Angstroms.

4. The method of claim 1 wherein forming a P-type source/drain extension includes implanting boron into the region implanted with germanium.

5. The method of claim 1 including implanting the germanium using sidewall spacers on a polysilicon gate structure.

6. The method of claim 1 including forming a strained source/drain extension.

7. The method of claim 1 including implanting a P-type impurity into a region already implanted with germanium.

8. The method of claim 7 including implanting germanium and P-type impurity at a ratio greater than 1 to 1.

9. The method of claim 8 including implanting germanium and P-type impurity at a ratio of approximately 4 to 1.

10. The method of claim 9 wherein implanting P-type impurities includes implanting boron impurities.

11. A semiconductor structure comprising:

a gate; and

an implanted region including both germanium and P-type impurities.

12. The structure of claim 11 wherein the ratio of germanium to P-type impurities is greater than one to one.

13. The structure of claim 12 wherein the ratio of germanium to P-type impurities is approximately four to one.

14. The structure of claim 13 wherein said P-type impurities are boron impurities.

15. The structure of claim 11 wherein said germanium is implanted to a depth greater than about 150 Angstroms.

16. The structure of claim 11 wherein said implanted region is a source/drain extension.

17. The structure of claim 16 wherein said implanted region is a strained source/drain junction.

18. The structure of claim 11 including a polysilicon gate.

19. The structure of claim 18 including a polysilicon gate with side wall spacers.

20. An integrated circuit comprising:

a semiconductor structure;

a gate formed on said semiconductor structure; and

a source and a drain region, said source and drain region including both germanium and a P-type impurity, said source and drain region being strained.

21. The circuit of claim 20 wherein the ratio of germanium to P-type impurities is greater than one to one.

22. The circuit of claim 20 wherein the ratio of germanium to P-type impurities is approximately four to one.

23. The circuit of claim 20 wherein said P-type impurities are boron impurities.

24. The circuit of claim 20 wherein said source/drain region that includes both boron and germanium is a source/drain extension.